## FEATURES

Ultrawideband frequency range: $\mathbf{1 0 0} \mathbf{~ M H z}$ to $\mathbf{4 0} \mathbf{~ G H z}$
Reflective design
Low insertion loss: 1.5 dB at $\mathbf{4 0} \mathbf{~ G H z}$
High isolation: $\mathbf{3 7} \mathbf{~ d B}$ at 40 GHz
High input linearity
1 dB compression (P1dB): 29.4 dBm typical
Third-order intercept (IP3): 50 dBm typical
High power handling: $\mathbf{2 7} \mathbf{~ d B m}$ through path
ESD sensitivity: TBD
No low frequency spurious
RF settling time ( 0.1 dB final RF output): TBD


## APPLICATIONS

## Test instrumentation

Military radios, radars, electronic counter measures (ECMs) Cellular infrastructure

## GENERAL DESCRIPTION

The ADRF5024 is a general-purpose, single-pole, double-throw (SPDT) switch manufactured using a silicon process. It comes in a $2.25 \mathrm{~mm} \times 2.25 \mathrm{~mm}, 12$-lead land grid array (LGA) package and provides high isolation and low insertion loss from 100 MHz to 40 GHz .

FUNCTIONAL BLOCK DIAGRAM


Figure 1.

This broadband switch requires dual supply voltages, +3.3 V and -3.3 V, and provides CMOS/LVTTL logic-compatible control.

## COMPARABLE PARTS

View a parametric search of comparable parts.

## DOCUMENTATION $\square$

## Data Sheet

- ADRF5024: Silicon SPDT Switch 100 MHz to 40 GHz Data Sheet


## DESIGN RESOURCES

- ADRF5024 Material Declaration
- PCN-PDN Information
- Quality And Reliability
- Symbols and Footprints


## DISCUSSIONS

View all ADRF5024 EngineerZone Discussions.
SAMPLE AND BUY $\square$
Visit the product page to see pricing options.

## TECHNICAL SUPPORT $\square$

Submit a technical question or find your regional support number.

## DOCUMENT FEEDBACK

Submit feedback for this data sheet.

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## SPECIFICATIONS

$\mathrm{V}_{\mathrm{DD}}=3.3 \mathrm{~V}, \mathrm{~V}_{\mathrm{SS}}=-3.3 \mathrm{~V}, \mathrm{~V}_{\mathrm{CTL}}=0 \mathrm{~V}$ or $3.3 \mathrm{~V}, \mathrm{~T}_{\mathrm{CASE}}=25^{\circ} \mathrm{C}, 50 \Omega$ system, unless otherwise noted.
Table 1.

| Parameter | Symbol | Test Conditions/Comments | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| FREQUENCY RANGE |  |  | 100 |  | 40,000 | MHz |
| INSERTION LOSS <br> Between RFC and RF1/RF2 (On) |  | 100 MHz to 10 GHz <br> 10 GHz to 30 GHz <br> 30 GHz to 40 GHz |  | $\begin{aligned} & 0.8 \\ & 1.3 \\ & 1.75 \end{aligned}$ |  | dB <br> dB <br> dB |
| ISOLATION <br> Between RFC and RF1/RF2 (Off) |  | 100 MHz to 10 GHz <br> 10 GHz to 30 GHz <br> 30 GHz to 40 GHz |  | $\begin{aligned} & 45 \\ & 41 \\ & 37 \end{aligned}$ |  | $\begin{aligned} & \mathrm{dB} \\ & \mathrm{~dB} \\ & \mathrm{~dB} \end{aligned}$ |
| RETURN LOSS RFC and RF1/RF2 (On) |  | 100 MHz to 10 GHz <br> 10 GHz to 30 GHz <br> 30 GHz to 40 GHz |  | $\begin{aligned} & 27 \\ & 12 \\ & 10 \\ & \hline \end{aligned}$ |  | $\begin{aligned} & \mathrm{dB} \\ & \mathrm{~dB} \\ & \mathrm{~dB} \end{aligned}$ |
| SWITCHING <br> Rise and Fall Time On and Off Time Settling Time 0.1 dB 0.05 dB | $\mathrm{t}_{\text {RISE, }} \mathrm{t}_{\text {fall }}$ ton, toff | $10 \%$ to $90 \%$ of RF output <br> $50 \% \mathrm{~V}$ сть to $90 \%$ of RF output <br> $50 \% \mathrm{~V}_{\text {ctL }}$ to 0.1 dB of final RF output <br> $50 \%$ VCtL to 0.05 dB of final RF output |  | $\begin{aligned} & 2 \\ & 9 \\ & \text { TBD } \\ & \text { TBD } \end{aligned}$ |  | ns <br> ns <br> ns |
| INPUT LINEARITY <br> 1 dB Power Compression Third-Order Intercept | $\begin{aligned} & \mathrm{P} 1 \mathrm{~dB} \\ & \mathrm{IP} 3 \\ & \hline \end{aligned}$ |  |  | $\begin{aligned} & 29.4 \\ & 50 \end{aligned}$ |  | $\begin{aligned} & \mathrm{dBm} \\ & \mathrm{dBm} \end{aligned}$ |
| SUPPLY CURRENT <br> Positive Supply Current Negative Supply Current | $\begin{aligned} & \mathrm{loD} \\ & \mathrm{I}_{\mathrm{SS}} \end{aligned}$ | VDD, VSS pins |  | $\begin{aligned} & 14 \\ & 120 \end{aligned}$ |  | $\begin{aligned} & \mu \mathrm{A} \\ & \mu \mathrm{~A} \end{aligned}$ |
| DIGITAL CONTROL INPUTS <br> Voltage <br> Low <br> High <br> Current <br> Low and High | $\mathrm{V}_{\mathrm{INL}}$ <br> $\mathrm{V}_{\mathrm{INH}}$ <br> IINL, IINH | CTRL pin | $\begin{aligned} & 0 \\ & \text { TBD } \end{aligned}$ | $<1$ | $\begin{aligned} & \text { TBD } \\ & 3.3 \end{aligned}$ | V V <br> $\mu \mathrm{A}$ |
| RECOMMENDED OPERATING CONDITONS <br> Supply Voltage Positive Negative <br> Digital Control Voltage RF Input Power Through Path <br> Hot Switching <br> Case Temperature | $V_{D D}$ <br> $V_{s s}$ <br> $V_{\text {cti }}$ <br> Pin <br> $\mathrm{T}_{\text {CASE }}$ | $\mathrm{f}=100 \mathrm{MHz} \text { to } 40 \mathrm{GHz}, \mathrm{~T}_{\text {CASE }}=85^{\circ} \mathrm{C}$ <br> RF signal is applied to RFC or through connected RF1/RF2 <br> RF signal is present at RFC while switching between RF1 and RF2 | $\begin{aligned} & 3.15 \\ & -3.45 \\ & 0 \\ & \\ & \\ & -40 \end{aligned}$ |  | $\begin{aligned} & 3.45 \\ & -3.15 \\ & V_{D D} \\ & 27 \\ & 27 \\ & +85 \end{aligned}$ | V <br> V <br> V <br> dBm <br> dBm <br> ${ }^{\circ} \mathrm{C}$ |

## ABSOLUTE MAXIMUM RATINGS

For recommended operating conditions, see Table 1.
Table 2.

| Parameter | Rating |
| :--- | :--- |
| Positive Supply Voltage | -0.5 V to +3.6 V |
| Negative Supply Voltage | -3.6 V to +0.5 V |
| Digital Control Input Voltage | -0.5 V to VDD +0.5 V |
| RF Input Power ( $\mathrm{f}=100 \mathrm{MHz}$ to 40 GHz, |  |
| $\quad$ TCASE $=85^{\circ} \mathrm{C}$ ) |  |
| Through Path | 28 dBm |
| $\quad$ Hot Switching | 28 dBm |
| Temperature |  |
| $\quad$ Junction, T J | $135^{\circ} \mathrm{C}$ |
| $\quad$ Storage | $-65^{\circ} \mathrm{C}$ to $+150^{\circ} \mathrm{C}$ |
| $\quad$ Reflow (MSL3 Rating) | $260^{\circ} \mathrm{C}$ |
| Junction to Case Thermal Resistance, $\theta_{\mathrm{Jc}}$ |  |
| $\quad$ Through Path | $\mathrm{TBD}{ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| ESD Sensitivity |  |
| $\quad$ Human Body Model (HBM) | TBD |

## PIN CONFIGURATION AND FUNCTION DESCRIPTIONS



## NOTES

1. THE EXPOSED PAD MUST BE CONNECTED TO THE RF/DC GROUND OF THE PRINTED CIRCUIT BOARD (PCB).

Figure 2. Pin Configuration (Top View)
Table 3. Pin Function Descriptions

| Pin No. | Mnemonic | Description |
| :--- | :--- | :--- |
| $1,3,4,6,10,12$ | GND | Ground. These pins must be connected to the RF/dc ground of the printed circuit board (PCB). |
| 2 | RFC | RF Common Port. This pin is dc-coupled to 0 V and ac matched to $50 \Omega$. No dc blocking capacitor is <br> necessary when the RF line potential is equal to 0 V dc. |
| 5 | RF1 | RF Throw Port 1. This pin is dc-coupled to 0 V and ac matched to $50 \Omega$. No dc blocking capacitor is <br> necessary when the RF line potential is equal to $0 \mathrm{~V} \mathrm{dc}$. <br> Positive Supply Voltage Pin. |
| 7 | VDD | CTRL |
| 8 | Control Input. |  |
| 9 | VSS | Negative Supply Voltage Pin. <br> RF Throw Port 2. This pin is dc-coupled to 0 V and ac matched to $50 \Omega$. No dc blocking capacitor is <br> necessary when the RF line potential is equal to 0 V dc. |
|  | EPAD | Exposed Pad. The exposed pad must be connected to the RF/dc ground of the printed circuit board (PCB). |

## INTERFACE SCHEMATICS



Figure 3. RF Pin Interface Schematic


Figure 4. Digital Pin Interface Schematic

## TYPICAL PERFORMANCE CHARCTERISTICS INSERTION LOSS, RETURN LOSS, AND ISOLATION

## TBD

## TBD



TBD


TBD

## Preliminary Technical Data

## TYPICAL PERFORMANCE CHARCTERISTICS

INPUT POWER COMPRESSION AND THIRD ORDER INTERCEPT


TBD

## THEORY OF OPERATION

The ADRF5024 requires a positive supply voltage applied to the VDD pin and a negative supply voltage applied to the VSS pin. A driver is incorporated on die to perform logic functions internally and to provide the user with the advantage of a simplified control interface. The driver features a single digital control input pin, CTRL that controls the state of RF paths. Depending on the logic level applied to the CTRL pin, one RF path is in insertion loss state while the other path is in isolation state (see Table 4). The insertion loss path conducts the RF signal equally well in both directions between RF throw port and RF common port while the isolation path provides high loss between RF throw port and the insertion loss path. RF throw port becomes open reflective in off state.

Table 4. Control Voltage Truth Table

| Digital Control Input | RF Paths |  |
| :--- | :--- | :--- |
| V1 | RF1 to RFC | RF2 to RFC |
| Low | Isolation (off) | Insertion loss (on) |
| High | Insertion loss (on) | Isolation (off) |

The ideal power-up sequence is as follows:

1. Connect ground.
2. Power up VDD and VSS. The relative order is not important.
3. Power up the digital control inputs. The relative order of the logic control inputs is not important. However, powering the digital control inputs before the VDD supply can inadvertently forward bias and damage the internal ESD protection structures.
4. Apply an RF input signal. The design is bidirectional; the RF input signal can be applied to the RFC port while the RF throw ports are outputs or vice versa. All of the RF ports are dc-coupled to 0 V , and no dc blocking is required at the RF ports when the RF line potential is equal to 0 V .

## OUTLINE DIMENSIONS



Figure 12-Terminal Land Grid Array [LGA]
$2.25 \mathrm{~mm} \times 2.25 \mathrm{~mm}$ Body and 0.75 mm Package Height
(CC-12-3)
Dimensions shown in millimeters

